

What is claimed is:

1. A method of manufacturing semiconductor devices, comprising:
forming an isolating film on a given region of a semiconductor substrate to
5 define a first region and a second region;
forming a first oxide film on the entire structure and then removing the first
oxide film from the second region using a photoresist film pattern;
removing the photoresist film pattern using a solvent;
implementing an oxidization process to form a second oxide film on the
10 semiconductor substrate in the second region;
forming a polysilicon film on the entire structure and then patterning the
polysilicon film to form gate electrodes in the first and second regions, respectively,
and
implementing an impurity ion implantation process to form junction regions at
15 given regions on the semiconductor substrate.

2. The method as claimed in claim 1, wherein the first oxide film is
formed thicker than the second oxide film.

20 3. The method as claimed in claim 1, wherein the photoresist film is
formed using an i-line series photoresist material.

4. The method as claimed in claim 1, wherein the solvent includes any
one of ethylcellsoluve acetate (ECA), methylamyl ketone (MAK), ethyl pyruvate
25 (EP), ethyl lactate (EL), 3-methylmethoxy propionate (MMP),
propyleneglycomonomethyl ether (PGME), propyleneglycol-monomethylether
acetate (PGMEA) and ethoxyethyl propionate (EEP).

5. The method as claimed in claim 1, wherein the polysilicon film is
30 formed without applying a vacuum and is formed using SiH_4 gas or Si_2H_6 gas at a
temperature ranging from about 580°C to about 630°C .